



UTRON

Rev. 1.7

UT62L1024

128K X 8 BIT LOW POWER CMOS SRAM

FEATURES

- Access time : 35/55/70ns (max.)
- Low power consumption :
Operating : 40/35/30 mA (typical)
Standby : 2.5μA (typical) L-version
0.5μA (typical) LL-version
- Power supply range : 2.7V to 3.6V
- All inputs and outputs TTL compatible
- Fully static operation
- Three state outputs
- Data retention voltage : 2V (min.)
- Package : 32-pin 600 mil PDIP
32-pin 450 mil SOP
32-pin 8x20 mm TSOP-1
32-pin 8x13.4 mm STSOP

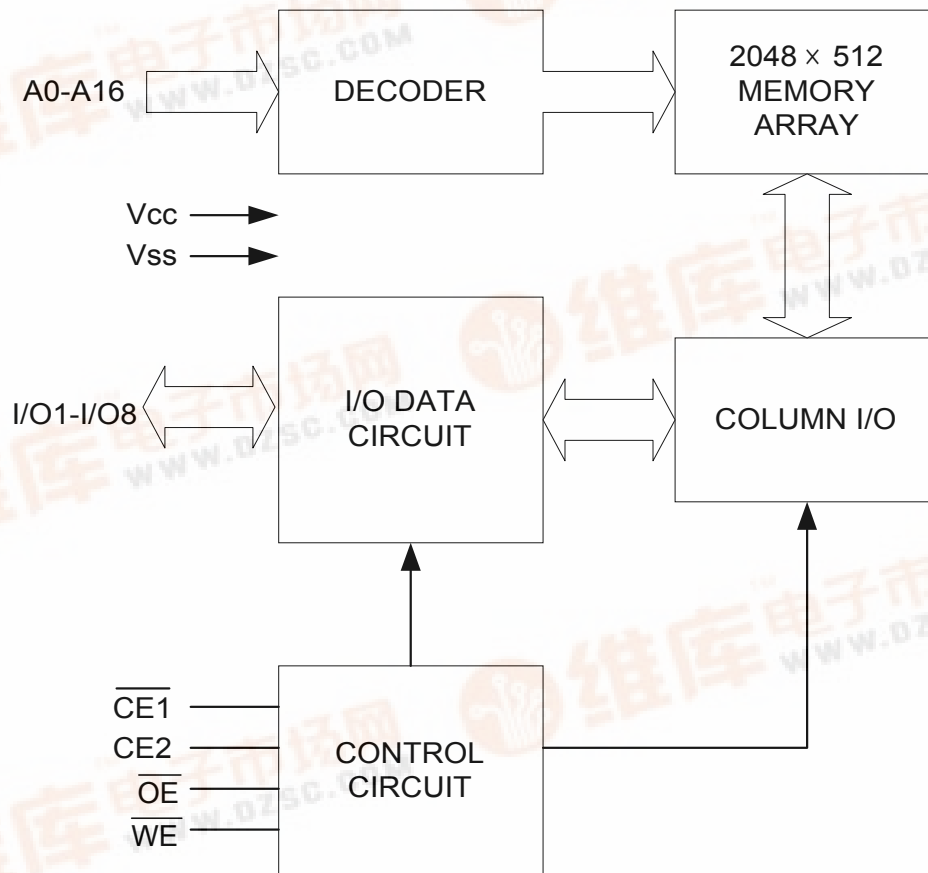
GENERAL DESCRIPTION

The UT62L1024 is a 1,048,576-bit low power CMOS static random access memory organized as 131,072 words by 8 bits. It is fabricated using high performance, high reliability CMOS technology.

Easy memory expansion is provided by using two chip enable input.($\overline{CE1}$, $CE2$) It is particularly well suited for battery back-up nonvolatile memory application.

The UT62L1024 operates from a single 2.7V~3.6V power supply and all inputs and outputs are fully TTL compatible.

FUNCTIONAL BLOCK DIAGRAM





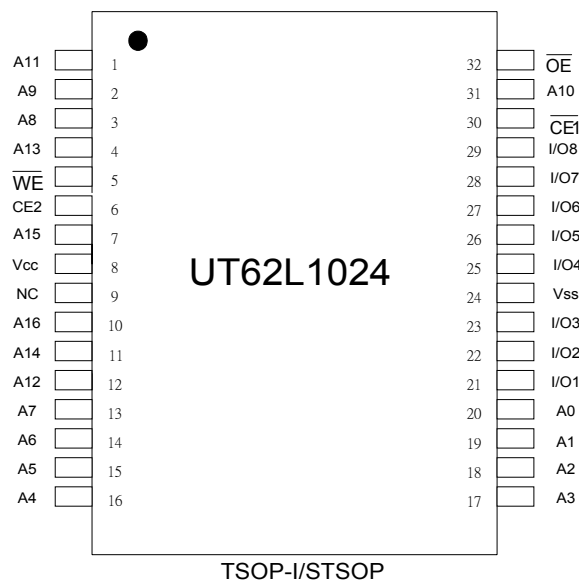
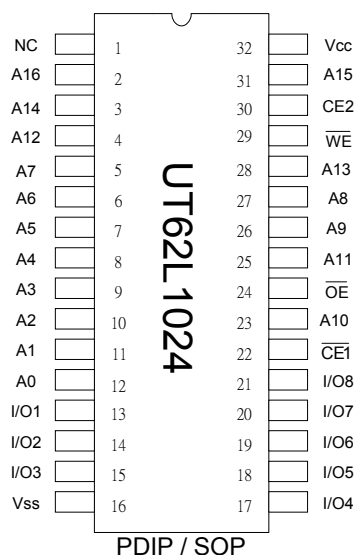
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PIN CONFIGURATION



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A16	Address Inputs
I/O1 - I/O8	Data Inputs/Outputs
$\overline{CE1}$, CE2	Chip enable 1,2 Inputs
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable Input
V _{CC}	Power Supply
V _{SS}	Ground
NC	No Connection



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ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Terminal Voltage with Respect to V _{SS}	V _{TERM}	-0.5 to +4.6	V
Operating Temperature	T _A	0 to +70	°C
Storage Temperature	T _{STG}	-65 to +150	°C
Power Dissipation	P _D	1	W
DC Output Current	I _{OUT}	50	mA
Soldering Temperature (under 10 sec)	T _{solder}	260	°C

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	$\overline{CE1}$	CE2	$\overline{OE}$	$\overline{WE}$	I/O OPERATION	SUPPLY CURRENT
Standby	H	X	X	X	High - Z	I _{SB} , I _{SB1}
Standby	X	L	X	X	High - Z	I _{SB} , I _{SB1}
Output Disable	L	H	H	H	High - Z	I _{CC} , I _{CC1}
Read	L	H	L	H	D _{OUT}	I _{CC} , I _{CC1}
Write	L	H	X	L	D _{IN}	I _{CC} , I _{CC1}

Note: H = V_{IH}, L = V_{IL}, X = Don't care.

DC ELECTRICAL CHARACTERISTICS (V_{CC} = 2.7V~3.6V, T_a = 0°C to +70°C)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input High Voltage	V _{IH}		2.0	-	V _{CC} +0.5	V
Input Low Voltage	V _{IL}		- 0.5	-	0.6	V
Input Leakage Current	I _{IL}	V _{SS} ≤ V _{IN} ≤ V _{CC}	- 1	-	1	μA
Output Leakage Current	I _{OL}	V _{SS} ≤ V _{I/O} ≤ V _{CC} $\overline{CE1} = V_{IH}$ or CE2 = V _{IL} or $\overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$	- 1	-	1	μA
Output High Voltage	V _{OH}	I _{OH} = - 1mA	2.2	-	-	V
Output Low Voltage	V _{OL}	I _{OL} = 4mA	-	-	0.4	V
Average Operating Power Supply Current	I _{CC}	Cycle time = Min. 100% Duty, $\overline{CE1} = V_{IL}$, CE2 = V _{IH} , I _{I/O} = 0mA	35	-	40	mA
			55	-	35	mA
			70	-	30	mA
	I _{CC1}	Cycle time = 1μs, 100% Duty, $\overline{CE1} \leq 0.2V$, CE2 ≥ V _{CC} -0.2V, I _{I/O} = 0mA	-	-	5	mA
Standby Power Supply Current	I _{SB}	$\overline{CE1} = V_{IH}$ or CE2 = V _{IL}	-	-	1.0	mA
	I _{SB1}	$\overline{CE1} \geq V_{CC}-0.2V$ or CE2 ≤ 0.2V	- L	-	2.5	100
			-	-	20*	μA
			- LL	-	0.5	40
					10*	μA

*Those parameters are for reference only under 50°C



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CAPACITANCE (Ta=25°C, f=1.0MHz)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
Input Capacitance	C _{IN}	-	6	pF
Input/Output Capacitance	C _{I/O}	-	8	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	0.4V to 2.4V
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	C _L =50pF, I _{OH} /I _{OL} =-1mA/2mA

AC ELECTRICAL CHARACTERISTICS (V_{CC} = 2.7V~3.6V, Ta = 0°C to +70°C)

(1) READ CYCLE

PARAMETER	SYMBOL	UT62L1024-35		UT62L1024-55		UT62L1024-70		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t _{RC}	35	-	55	-	70	-	ns
Address Access Time	t _{AA}	-	35	-	55	-	70	ns
Chip Enable Access Time	t _{ACE1} , t _{ACE2}	-	35	-	55	-	70	ns
Output Enable Access Time	t _{OE}	-	25	-	30	-	35	ns
Chip Enable to Output in Low-Z	t _{CLZ1} *, t _{CLZ2} *	10	-	10	-	10	-	ns
Output Enable to Output in Low-Z	t _{OLZ} *	5	-	5	-	5	-	ns
Chip Disable to Output in High-Z	t _{CHZ1} *, t _{CHZ2} *	-	25	-	30	-	35	ns
Output Disable to Output in High-Z	t _{OHZ} *	-	25	-	30	-	35	ns
Output Hold from Address Change	t _{OH}	5	-	5	-	5	-	ns

(2) WRITE CYCLE

PARAMETER	SYMBOL	UT62L1024-35		UT62L1024-55		UT62L1024-70		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t _{WC}	35	-	55	-	70	-	ns
Address Valid to End of Write	t _{AW}	30	-	50	-	60	-	ns
Chip Enable to End of Write	t _{CW1} , t _{CW2}	30	-	50	-	60	-	ns
Address Set-up Time	t _{AS}	0	-	0	-	0	-	ns
Write Pulse Width	t _{WP}	25	-	40	-	45	-	ns
Write Recovery Time	t _{WR}	0	-	0	-	0	-	ns
Data to Write Time Overlap	t _{DW}	20	-	25	-	30	-	ns
Data Hold from End of Write-Time	t _{DH}	0	-	0	-	0	-	ns
Output Active from End of Write	t _{OW} *	5	-	5	-	5	-	ns
Write to Output in High-Z	t _{WHZ} *	-	15	-	20	-	25	ns

*These parameters are guaranteed by device characterization, but not production tested.



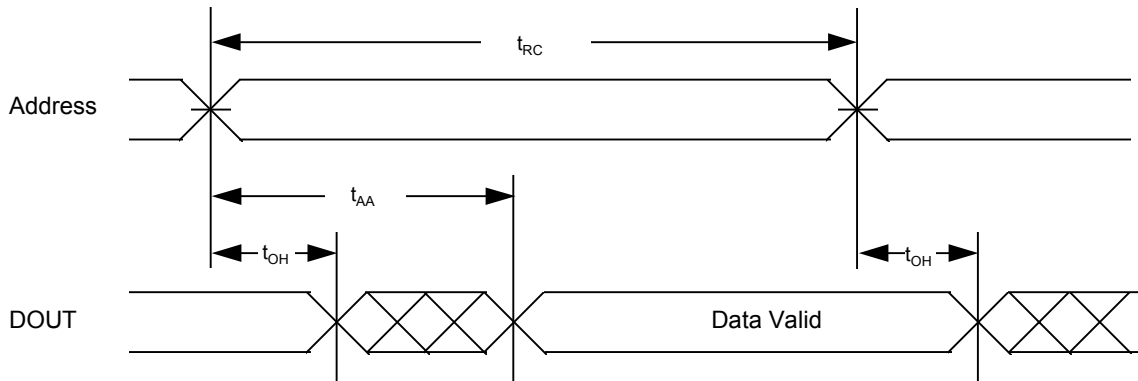
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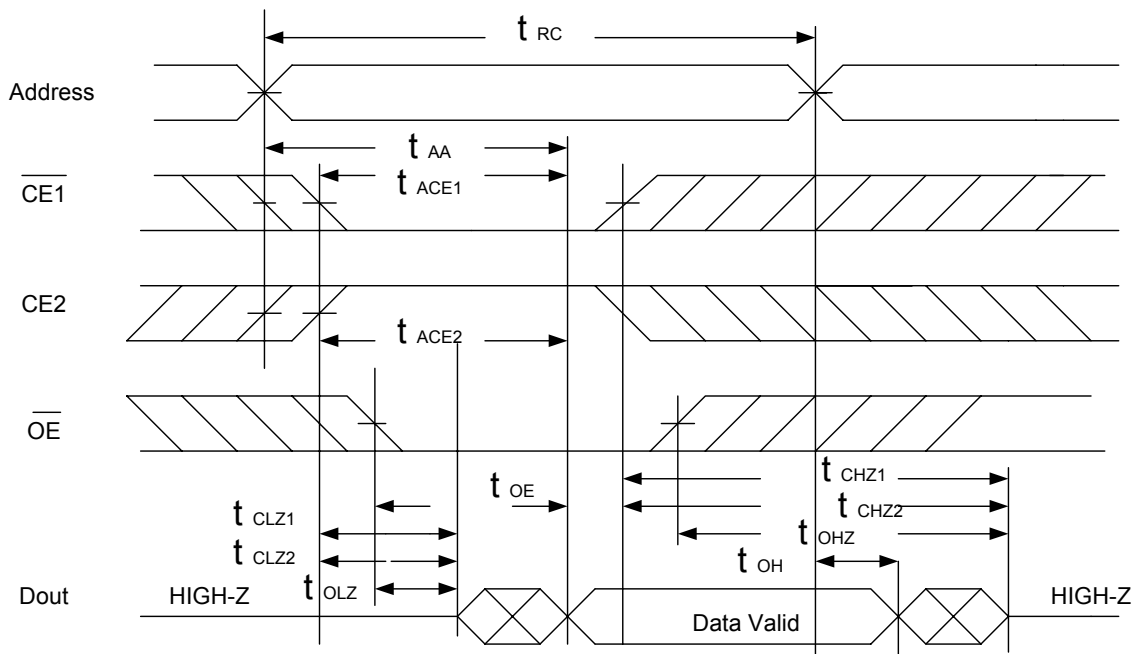
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TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2,4)



READ CYCLE 2 ($\overline{CE1}$, CE2 and $\overline{OE}$ Controlled) (1,3,5,6)



Notes :

1. $\overline{WE}$ is HIGH for a read cycle.
2. Device is continuously selected $\overline{OE}$, $\overline{CE1} = V_{IL}$ and $CE2 = V_{IH}$.
3. Address must be valid prior to or coincident with $\overline{CE1}$ LOW and CE2 high transition; otherwise t_{AA} is the limiting parameter.
4. $\overline{OE}$ is low.
5. t_{CLZ1} , t_{CLZ2} , t_{OLZ} , t_{CHZ1} , t_{CHZ2} and t_{OHZ} are specified with $C_L = 5pF$. Transition is measured $\pm 500mV$ from steady state.
6. At any given temperature and voltage condition, t_{CHZ1} is less than t_{CLZ1} , t_{CHZ2} is less than t_{CLZ2} , t_{OHZ} is less than t_{OLZ} .



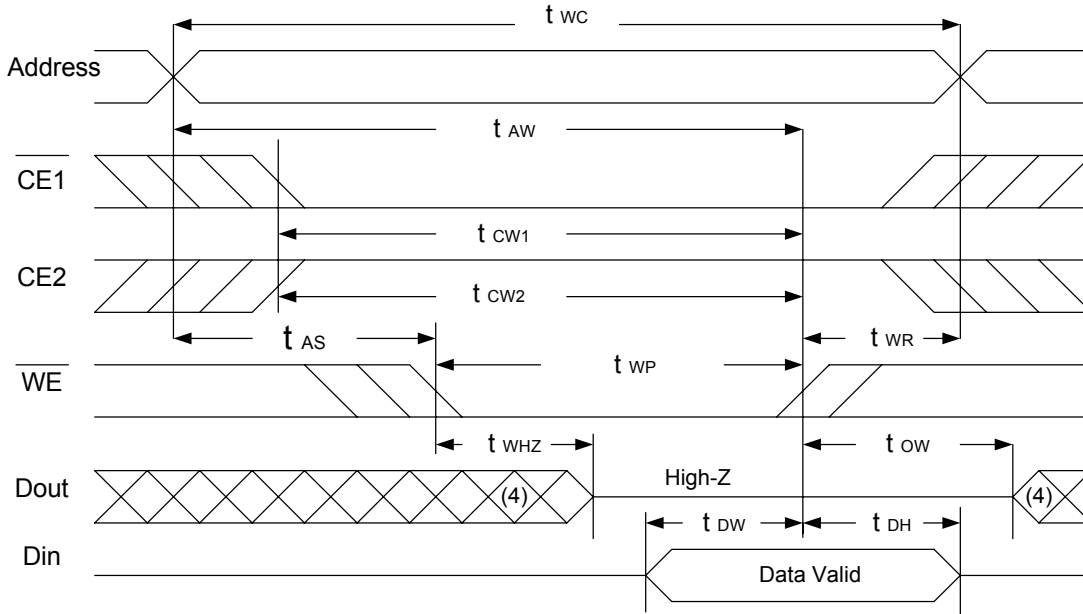
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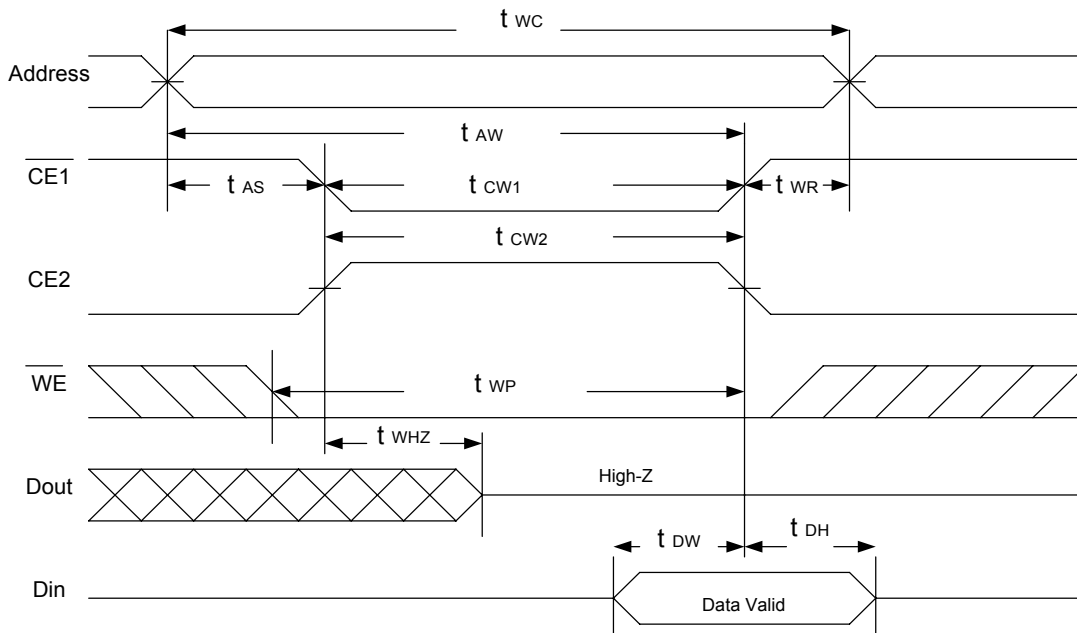
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WRITE CYCLE 1 ($\overline{WE}$ Controlled) (1,2,3,5)



WRITE CYCLE 2 ($\overline{CE1}$ and CE2 Controlled) (1,2,5)



Notes :

1. $\overline{WE}$ or $\overline{CE1}$ must be HIGH or CE2 must be LOW during all address transitions.
2. A write occurs during the overlap of a low $\overline{CE1}$, a high CE2 and a low $\overline{WE}$.
3. During a $\overline{WE}$ controlled with write cycle with $\overline{OE}$ LOW, t_{WP} must be greater than $t_{WHZ} + t_{DW}$ to allow the I/O drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
4. If the $\overline{CE1}$ LOW transition occurs simultaneously with or after $\overline{WE}$ LOW transition, the outputs remain in a high Impedance state.
6. t_{OW} and t_{WHZ} are specified with $C_L = 5pF$. Transition is measured $\pm 500mV$ from steady state.



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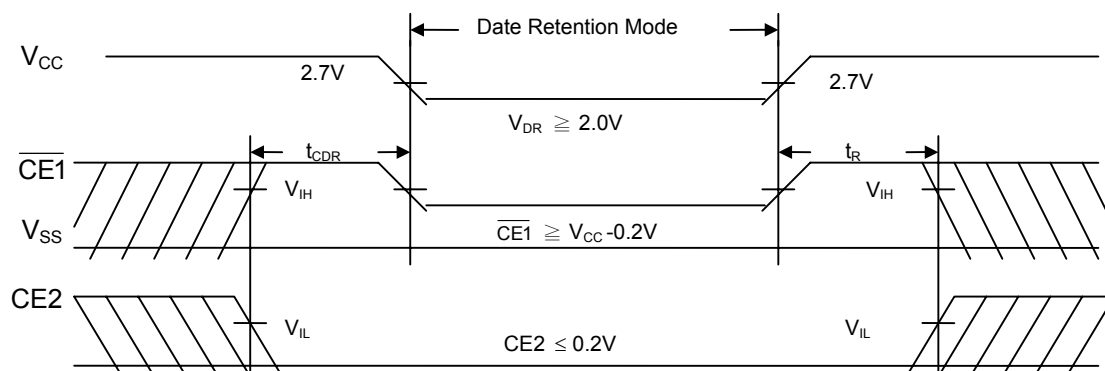
DATA RETENTION CHARACTERISTICS (Ta = 0°C to +70°C)

PARAMETER	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Vcc for Data Retention	V _{DR}	$\overline{CE1} \geq V_{CC}-0.2V$ or $CE2 \leq 0.2V$		2.0	-	3.3	V
Data Retention Current	I _{DR}	Vcc=2V	- L	-	1	40	μA
						20*	
		$\overline{CE1} \geq V_{CC}-0.2V$ or $CE2 \leq 0.2V$	- LL	-	0.5	20	μA
						5*	
Chip Disable to Data Retention Time	t _{CDR}	See Data Retention Waveforms (below)		0	-	-	ns
Recovery Time	t _R			t _{RC} *	-	-	ns

t_{RC}* = Read Cycle Time

*Those parameters are for reference only under 50°C

DATA RETENTION WAVEFORM





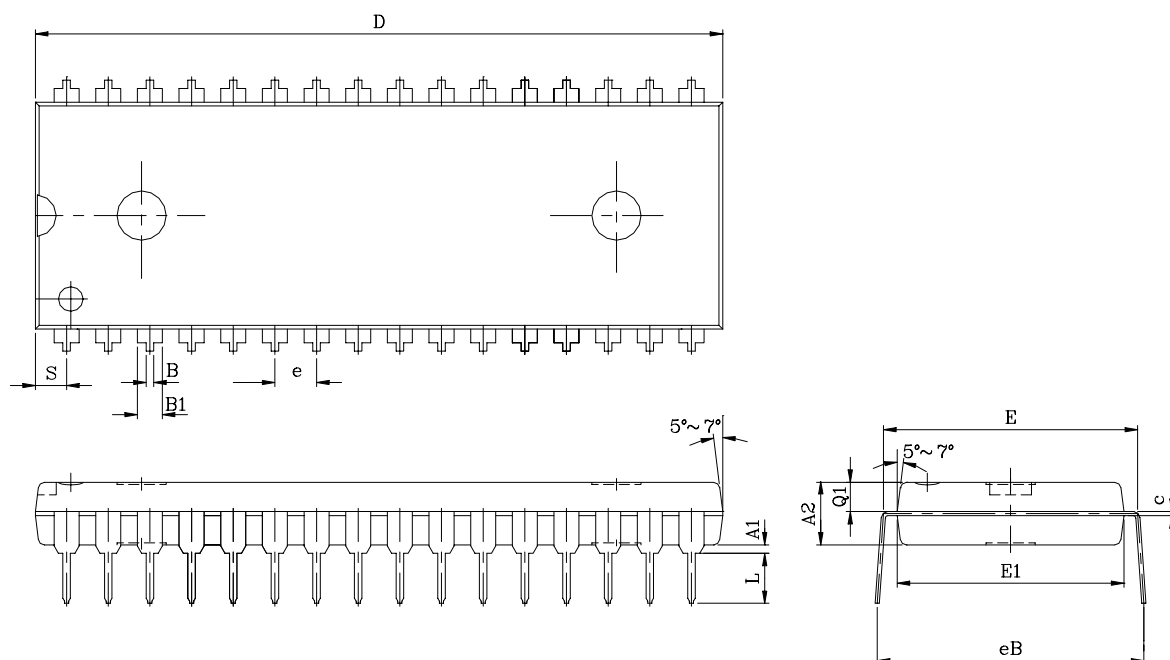
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PACKAGE OUTLINE DIMENSION

32 pin 600 mil PDIP Package Outline Dimension



UNIT SYMBOL	INCH(BASE)	MM(REF)
A1	0.010 (MIN)	0.254 (MIN)
A2	0.150 ± 0.005	3.810 ± 0.127
B	0.018 ± 0.005	0.457 ± 0.127
B1	0.050 ± 0.005	1.270 ± 0.127
c	0.010 ± 0.004	0.254 ± 0.102
D	1.650 ± 0.005	41.910 ± 0.127
E	0.600 ± 0.010	15.240 ± 0.254
E1	0.544 ± 0.004	13.818 ± 0.102
e	0.100 (TYP)	2.540 (TYP)
eB	0.640 ± 0.020	16.256 ± 0.508
L	0.130 ± 0.010	3.302 ± 0.254
S	0.075 ± 0.010	1.905 ± 0.254
Q1	0.070 ± 0.005	1.778 ± 0.127

Note:

1. D/E1/S DIMENSION DO NOT INCLUDE MOLD FLASH.



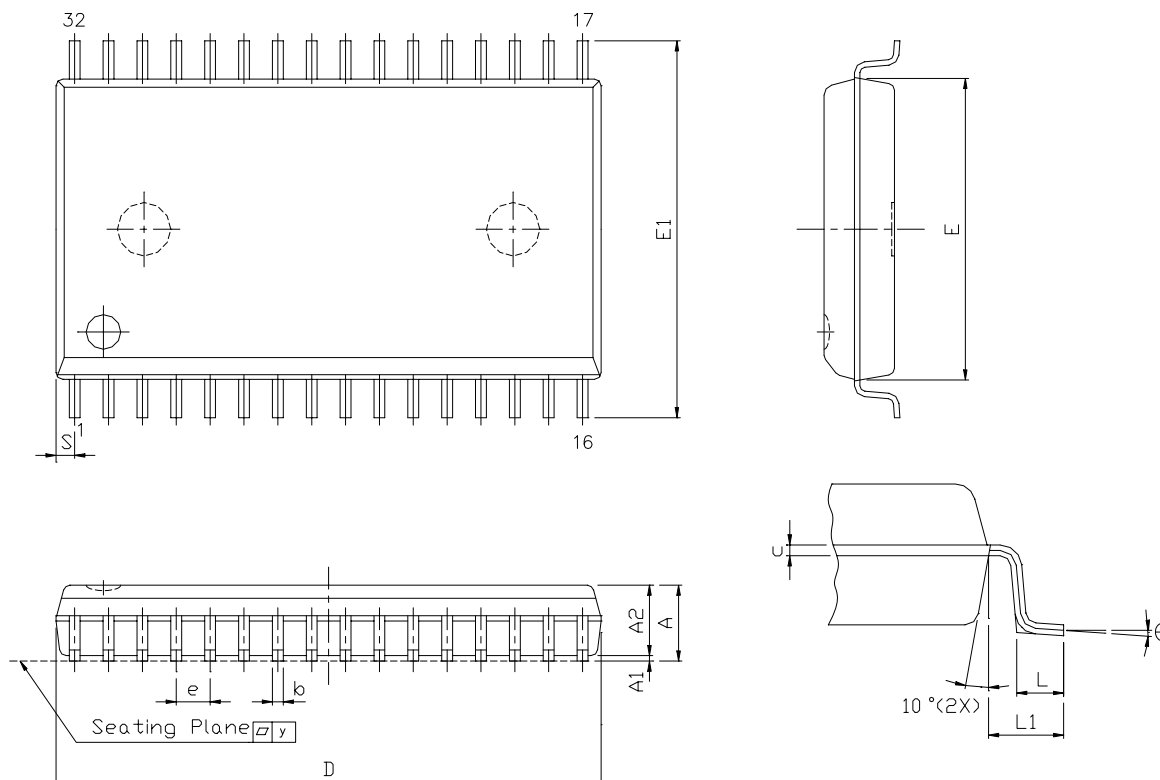
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32 pin 450mil SOP Package Outline Dimension



UNIT	INCH(BASE)	MM(REF)
SYMBOL		
A	0.118 (MAX)	2.997 (MAX)
A1	0.004(MIN)	0.102(MIN)
A2	0.111(MAX)	2.82(MAX)
b	0.016(TYP)	0.406(TYP)
c	0.008(TYP)	0.203(TYP)
D	0.817(MAX)	20.75(MAX)
E	0.445 ± 0.005	11.303 ± 0.127
E1	0.555 ± 0.012	14.097 ± 0.305
e	0.050(TYP)	1.270(TYP)
L	0.0347 ± 0.008	0.881 ± 0.203
L1	0.055 ± 0.008	1.397 ± 0.203
S	0.026(MAX)	0.066 (MAX)
y	0.004(MAX)	0.101(MAX)
Θ	0° -10°	0° -10°



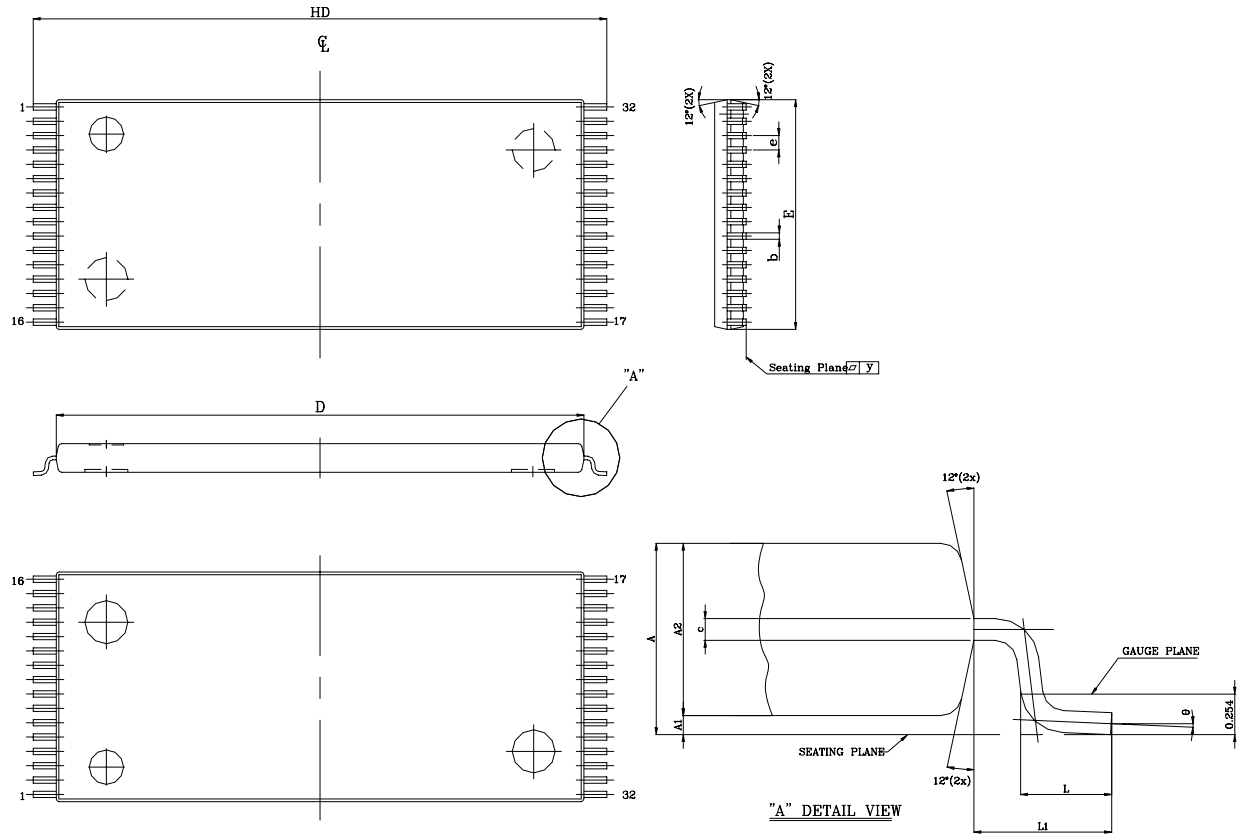
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32 pin TSOP-I Package Outline Dimension



UNIT	INCH(BASE)	MM(REF)
SYMBOL		
A	0.047 (MAX)	1.20 (MAX)
A1	0.004 ± 0.002	0.10 ± 0.05
A2	0.039 ± 0.002	1.00 ± 0.05
b	0.008 + 0.002 - 0.001	0.20 + 0.05 - 0.03
c	0.005 (TYP)	0.127 (TYP)
D	0.724 ± 0.004	18.40 ± 0.10
E	0.315 ± 0.004	8.00 ± 0.10
e	0.020 (TYP)	0.50 (TYP)
HD	0.787 ± 0.008	20.00 ± 0.20
L	0.0197 ± 0.004	0.50 ± 0.10
L1	0.0315 ± 0.004	0.08 ± 0.10
y	0.003 (MAX)	0.076 (MAX)
Θ	0°~5°	0°~5°



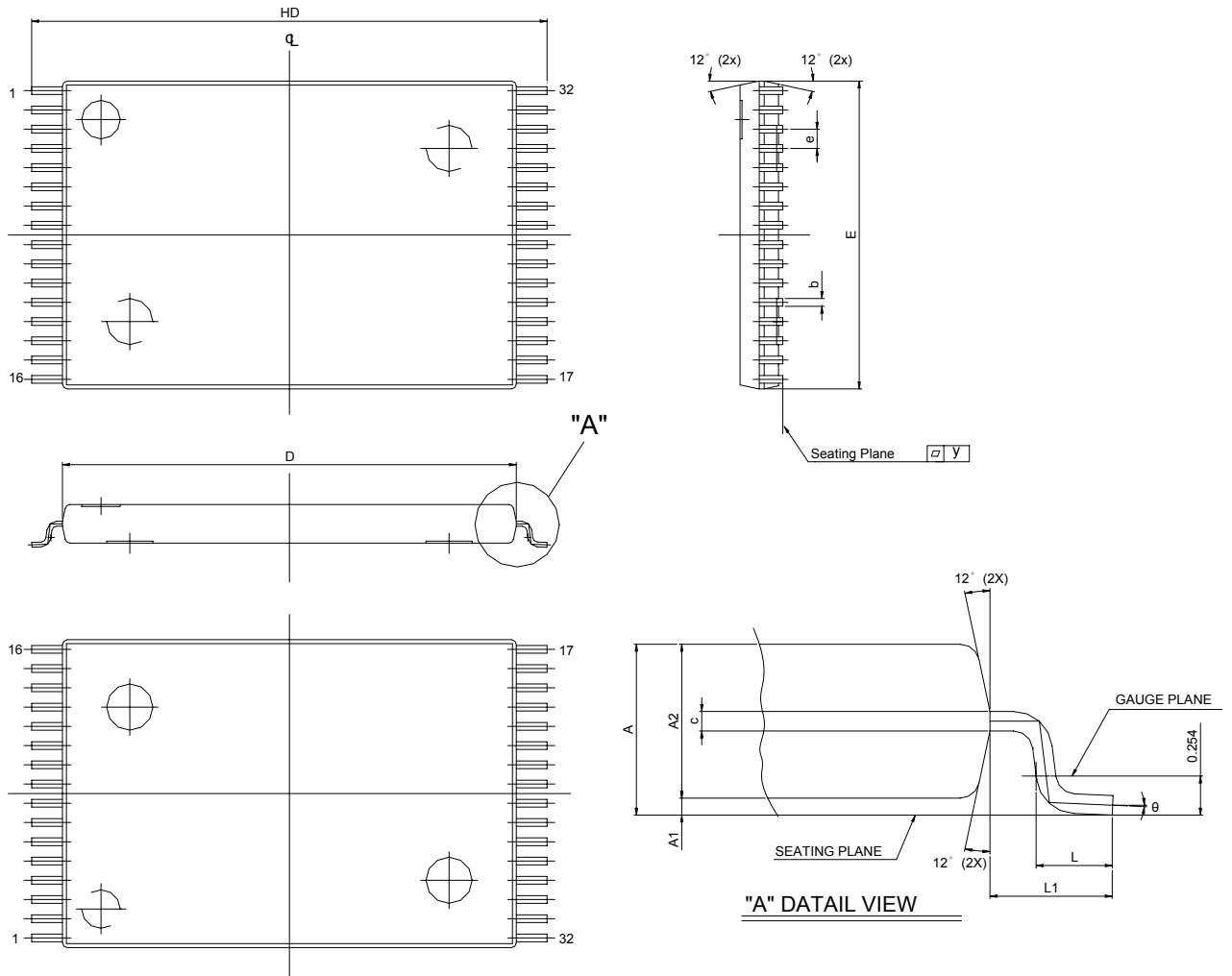
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128K X 8 BIT LOW POWER CMOS SRAM

32 pin 8mm x 13.4mm STSOP Package Outline Dimension



UNIT SYMBOL	INCH(BASE)	MM(REF)
A	0.049 (MAX)	1.25 (MAX)
A1	0.005 ± 0.002	0.130 ± 0.05
A2	0.039 ± 0.002	1.00 ± 0.05
b	0.008 ± 0.01	0.20 ± 0.025
c	0.005 (TYP)	0.127 (TYP)
D	0.465 ± 0.004	11.80 ± 0.10
E	0.315 ± 0.004	8.00 ± 0.10
e	0.020 (TYP)	0.50 (TYP)
HD	0.528 ± 0.008	13.40 ± 0.20
L	0.0197 ± 0.004	0.50 ± 0.10
L1	0.0315 ± 0.004	0.8 ± 0.10
y	0.003 (MAX)	0.076 (MAX)
θ	0° ~ 5°	0° ~ 5°





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ORDERING INFORMATION

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) (max) Ta = 50°C	PACKAGE
UT62L1024PC-35L	35	20	32 PIN PDIP
UT62L1024PC-35LL	35	10	32 PIN PDIP
UT62L1024PC-55L	55	20	32 PIN PDIP
UT62L1024PC-55LL	55	10	32 PIN PDIP
UT62L1024PC-70L	70	20	32 PIN PDIP
UT62L1024PC-70LL	70	10	32 PIN PDIP
UT62L1024SC-35L	35	20	32 PIN SOP
UT62L1024SC-35LL	35	10	32 PIN SOP
UT62L1024SC-55L	55	20	32 PIN SOP
UT62L1024SC-55LL	55	10	32 PIN SOP
UT62L1024SC-70L	70	20	32 PIN SOP
UT62L1024SC-70LL	70	10	32 PIN SOP
UT62L1024LC-35L	35	20	32 PIN TSOP-I
UT62L1024LC-35LL	35	10	32 PIN TSOP-I
UT62L1024LC-55L	55	20	32 PIN TSOP-I
UT62L1024LC-55LL	55	10	32 PIN TSOP-I
UT62L1024LC-70L	70	20	32 PIN TSOP-I
UT62L1024LC-70LL	70	10	32 PIN TSOP-I
UT62L1024LS-35L	35	20	32 PIN STSOP
UT62L1024LS-35LL	35	10	32 PIN STSOP
UT62L1024LS-55L	55	20	32 PIN STSOP
UT62L1024LS-55LL	55	10	32 PIN STSOP
UT62L1024LS-70L	70	20	32 PIN STSOP
UT62L1024LS-70LL	70	10	32 PIN STSOP



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REVISION HISTORY

REVISION	DESCRIPTION	DATE
Rev. 1.0	Original.	Jun. 01. 1997
Rev. 1.1	128Kx 8 Low Voltage CMOS SRAM 之TN8106 body 已作fine tunings,將 I_{SB1} 降為0.5uA(LL)、2uA(L)、Vcc range : 3.0V~3.6V	Apr. 05. 2000
Rev. 1.2	Add STSOP-I Package	Aug. 29. 2000
Rev. 1.3	Modify the format of power consumption	Sep. 01. 2000
Rev. 1.4	Add speed : -55ns	Dec. 01. 2000
Rev. 1.5	Vcc min 3.1→2.7V	Mar. 15. 2001
Rev. 1.6	1. The symbols CE1#, OE# & WE# are revised as $\overline{CE1}$, $\overline{OE}$ & $\overline{WE}$. 2. Add Icc value of 55ns range(access time) . 3. V_{OH} is revised as 2.2V. 4. I_{SB1} is revised as 100 μ s.	Jun. 26. 2001
Rev. 1.7	Revised 32 pin 8mmx13.4mm STSOP Package Outline Dimension.	Nov. 26. 2001



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